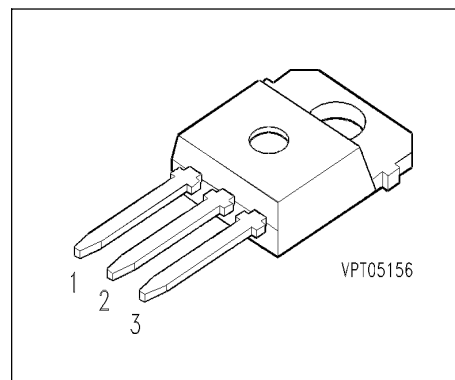


IGBT With Antiparallel Diode

Preliminary data sheet

- Low forward voltage drop
- High switching speed
- Low tail current
- Latch-up free
- Including fast free-wheel diode

Former Development ID: BUP 3JKD



Pin 1	Pin 2	Pin 3
G	C	E

Type	V_{CE}	I_C	Package	Ordering Code
BUP 311D	1200V	A	TO-218 AB	ON REQUEST

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CE}	1200	V
Collector-gate voltage	V_{CGR}		
$R_{GE} = 20\text{ k}\Omega$		1200	
Gate-emitter voltage	V_{GE}	± 20	
DC collector current	I_C		A
$T_C = 25\text{ }^{\circ}\text{C}$		20	
$T_C = 100\text{ }^{\circ}\text{C}$		12	
Pulsed collector current, $t_p = 1\text{ ms}$	I_{Cpuls}		
$T_C = 25\text{ }^{\circ}\text{C}$		40	
Diode forward current	I_F		
$T_C = 100\text{ }^{\circ}\text{C}$		tbd	
Pulsed diode current, $t_p = 1\text{ ms}$	I_{Fpuls}		
$T_C = 25\text{ }^{\circ}\text{C}$		tbd	
Power dissipation	P_{tot}		W
$T_C = 25\text{ }^{\circ}\text{C}$		125	
Chip or operating temperature	T_j	-55 ... + 150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 ... + 150	

Maximum Ratings

Parameter	Symbol	Values	Unit
Chip or operating temperature	T_j	-55 ... + 150	°C
Storage temperature	T_{stg}	-55 ... + 150	
IEC climatic category, DIN IEC 68-1	-	55 / 150 / 56	-

Thermal Resistance

Thermal resistance, junction - case	R_{thJC}	≤ 1	K/W
Diode thermal resistance, chip case	R_{thJCD}	≤ 2.5	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Gate threshold voltage $V_{GE} = V_{CE}, I_C = 0.3\text{ mA}, T_j = 25\text{ °C}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter saturation voltage $V_{GE} = 15\text{ V}, I_C = 8\text{ A}, T_j = 25\text{ °C}$	$V_{CE(sat)}$	-	2.5	3	
$V_{GE} = 15\text{ V}, I_C = 8\text{ A}, T_j = 125\text{ °C}$		-	3.1	3.7	
$V_{GE} = 15\text{ V}, I_C = 16\text{ A}, T_j = 25\text{ °C}$		-	3.4	-	
$V_{GE} = 15\text{ V}, I_C = 16\text{ A}, T_j = 125\text{ °C}$		-	4.3	-	
Zero gate voltage collector current $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 25\text{ °C}$	I_{CES}	-	-	0.4	mA
Gate-emitter leakage current $V_{GE} = 25\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	-	-	120	nA

AC Characteristics

Transconductance $V_{CE} = 20 \text{ V}$, $I_C = 8 \text{ A}$	g_{fs}	4	-	-	S
Input capacitance $V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$	C_{iss}	-	600	tbd	pF
Output capacitance $V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$	C_{oss}	-	60	tbd	
Reverse transfer capacitance $V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$	C_{rss}	-	38	tbd	

Electrical Characteristics, at $T_j = 25 \text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Switching Characteristics, Inductive Load at $T_j = 125 \text{ °C}$

Turn-on delay time $V_{CC} = 600 \text{ V}$, $V_{GE} = 15 \text{ V}$, $I_C = 8 \text{ A}$ $R_{Gon} = 150 \text{ } \Omega$	$t_{d(on)}$	-	55	tbd	ns
Rise time $V_{CC} = 600 \text{ V}$, $V_{GE} = 15 \text{ V}$, $I_C = 8 \text{ A}$ $R_{Gon} = 150 \text{ } \Omega$	t_r	-	50	tbd	
Turn-off delay time $V_{CC} = 600 \text{ V}$, $V_{GE} = -15 \text{ V}$, $I_C = 8 \text{ A}$ $R_{Goff} = 150 \text{ } \Omega$	$t_{d(off)}$	-	380	tbd	
Fall time $V_{CC} = 600 \text{ V}$, $V_{GE} = -15 \text{ V}$, $I_C = 8 \text{ A}$ $R_{Goff} = 150 \text{ } \Omega$	t_f	-	80	tbd	

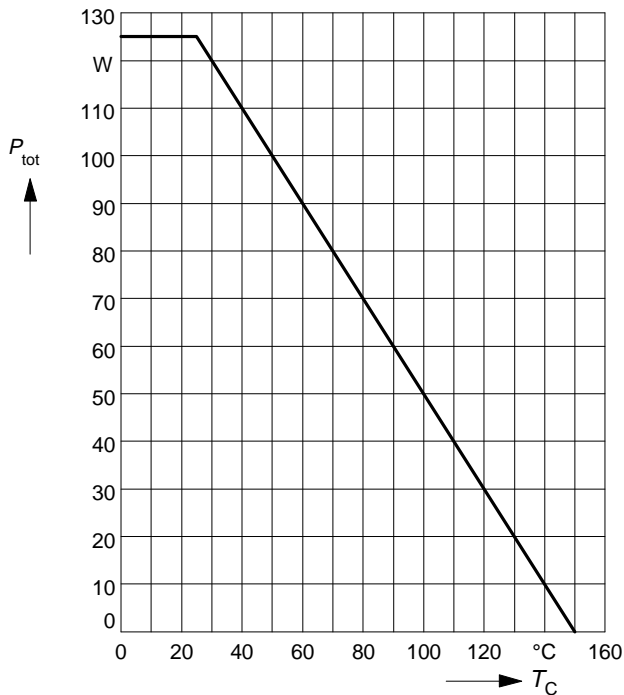
Free-Wheel Diode

Diode forward voltage $I_F = 8 \text{ A}$, $V_{GE} = 0 \text{ V}$, $T_j = 25 \text{ °C}$ $I_F = 8 \text{ A}$, $V_{GE} = 0 \text{ V}$, $T_j = 125 \text{ °C}$	V_F	- -	tbd tbd	tbd -	V
Reverse recovery time $I_F = 8 \text{ A}$, $V_R = -600 \text{ V}$, $V_{GE} = 0 \text{ V}$ $di_F/dt = -400 \text{ A/}\mu\text{s}$, $T_j = 25 \text{ °C}$	t_{rr}	-	tbd	tbd	ns
Reverse recovery charge $I_F = 15 \text{ A}$, $V_R = -600 \text{ V}$, $V_{GE} = 0 \text{ V}$ $di_F/dt = -400 \text{ A/}\mu\text{s}$ $T_j = 25 \text{ °C}$ $T_j = 125 \text{ °C}$	Q_{rr}	- -	tbd tbd	tbd tbd	μC

Power dissipation

$$P_{\text{tot}} = f(T_C)$$

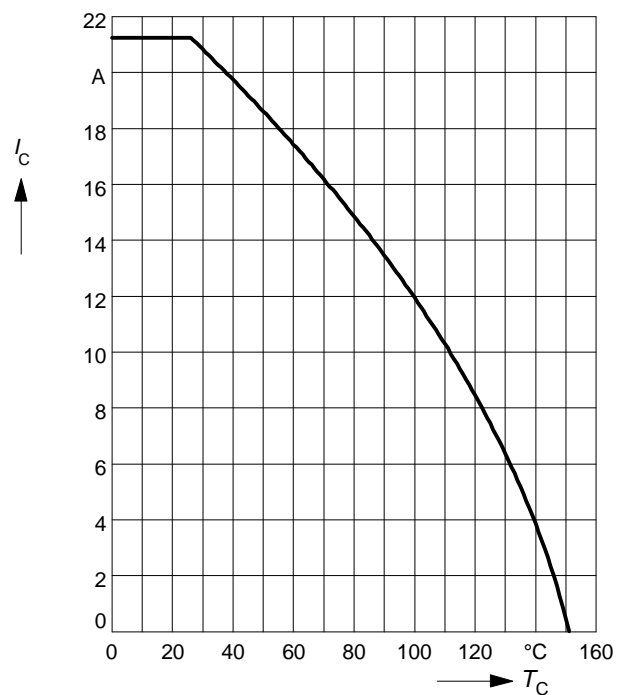
parameter: $T_j \leq 150^\circ\text{C}$



Collector current

$$I_C = f(T_C)$$

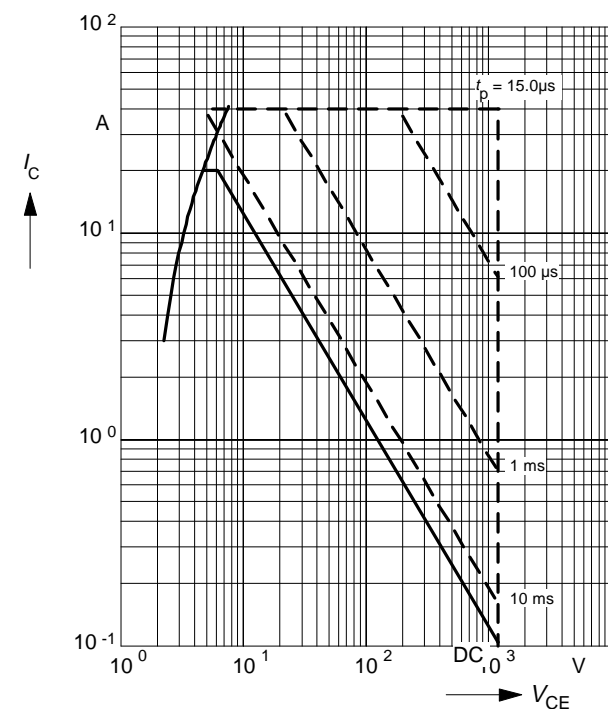
parameter: $V_{GE} \geq 15\text{ V}$, $T_j \leq 150^\circ\text{C}$



Safe operating area

$$I_C = f(V_{CE})$$

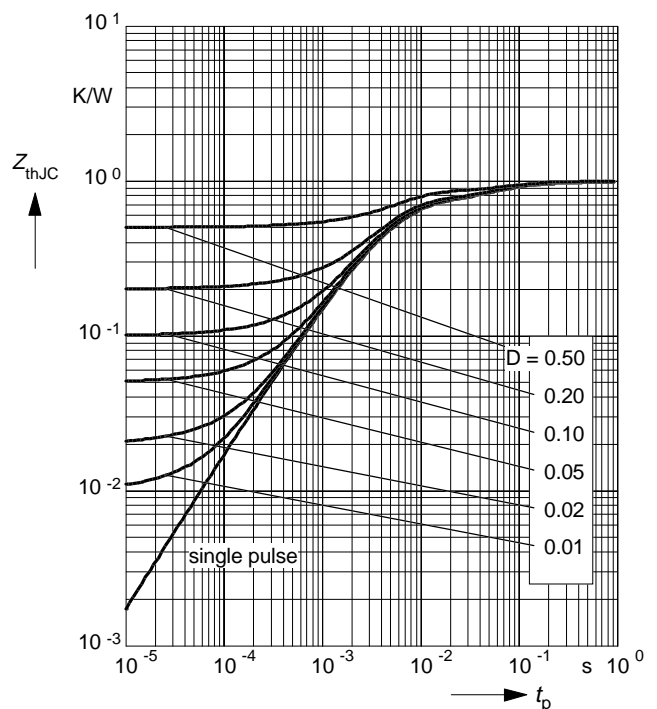
parameter: $D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$



Transient thermal impedance IGBT

$$Z_{\text{th JC}} = f(t_p)$$

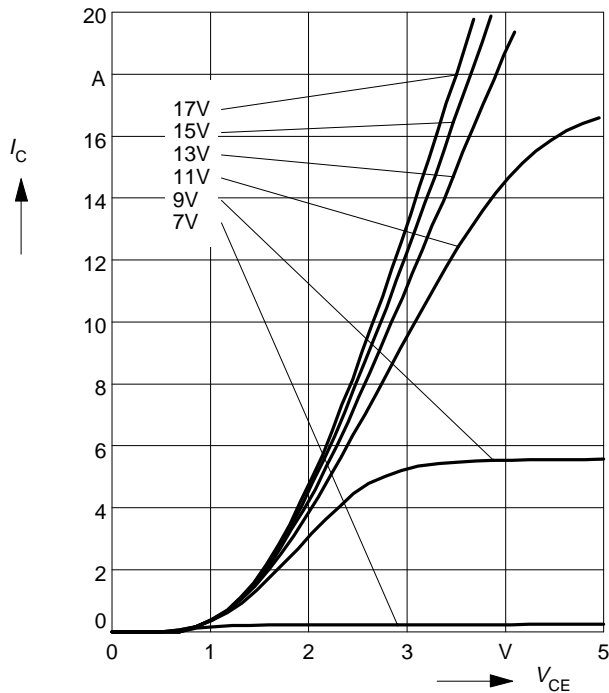
parameter: $D = t_p / T$



Typ. output characteristics

$$I_C = f(V_{CE})$$

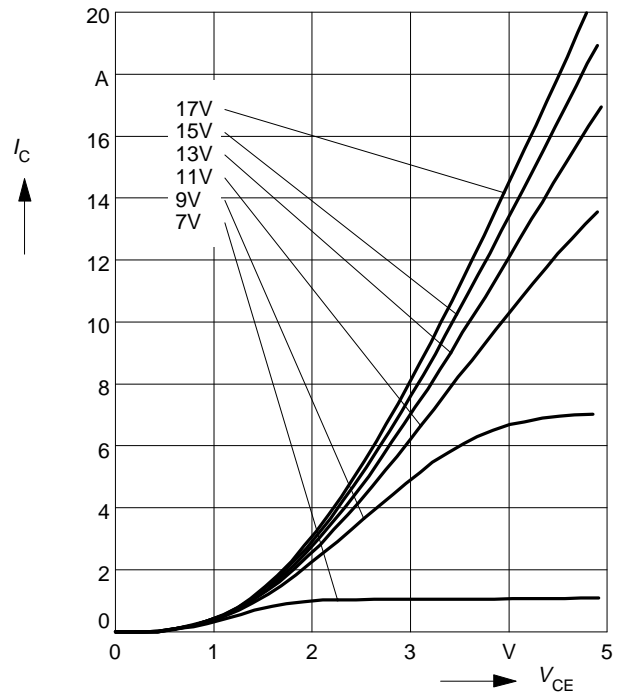
parameter: $t_p = 80 \mu s$, $T_j = 25^\circ C$



Typ. output characteristics

$$I_C = f(V_{CE})$$

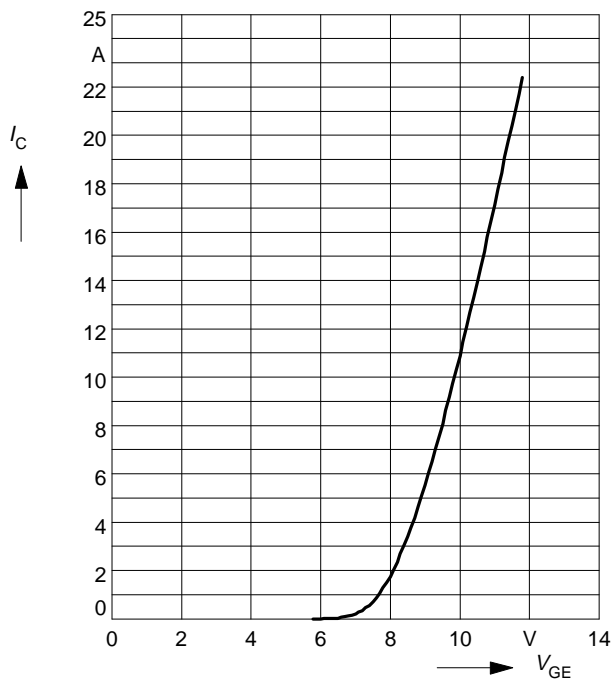
parameter: $t_p = 80 \mu s$, $T_j = 125^\circ C$



Typ. transfer characteristics

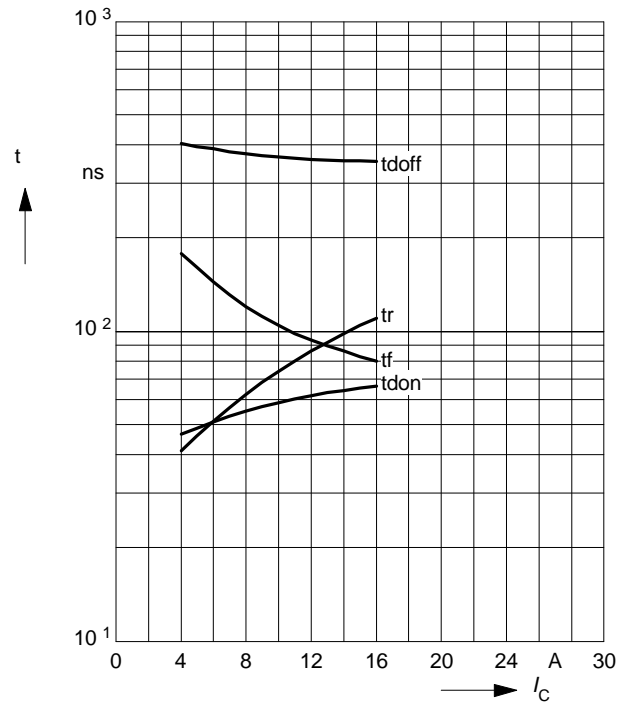
$$I_C = f(V_{GE})$$

parameter: $t_p = 80 \mu s$, $V_{CE} = 20 V$



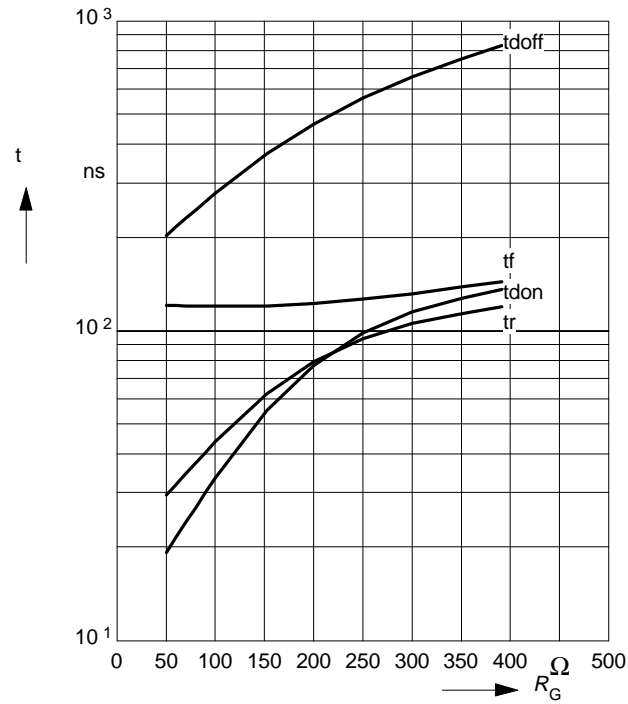
Typ. switching time

$t = f(I_C)$, inductive load, $T_j = 125^\circ\text{C}$
par.: $V_{CE}=600\text{V}$, $V_{GE} = \pm 15\text{V}$, $R_G = 153\Omega$



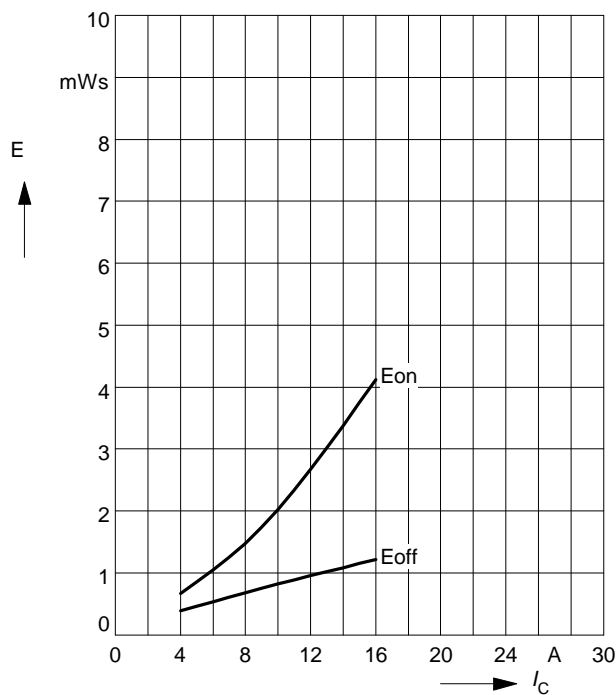
Typ. switching time

$t = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$
par.: $V_{CE}=600\text{V}$, $V_{GE} = \pm 15\text{V}$, $I_C = 8\text{ A}$



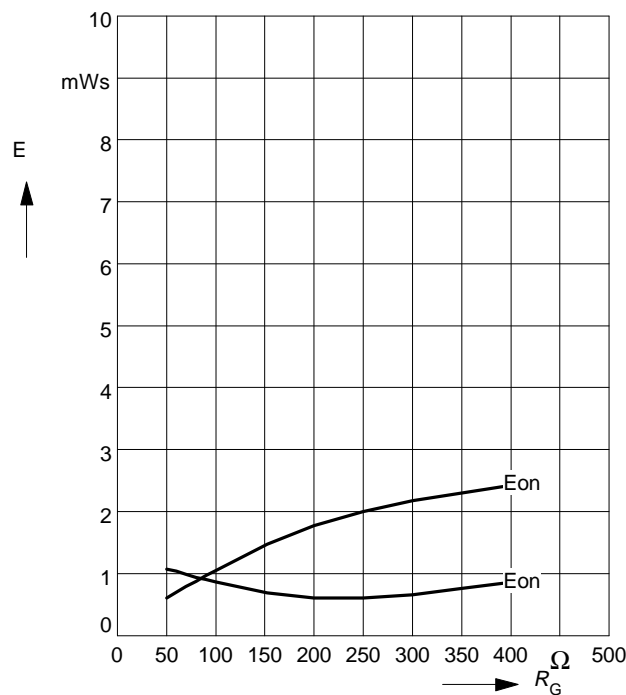
Typ. switching losses

$E = f(I_C)$, inductive load, $T_j = 125^\circ\text{C}$
par.: $V_{CE}=600\text{V}$, $V_{GE} = \pm 15\text{V}$, $R_G = 153\Omega$



Typ. switching losses

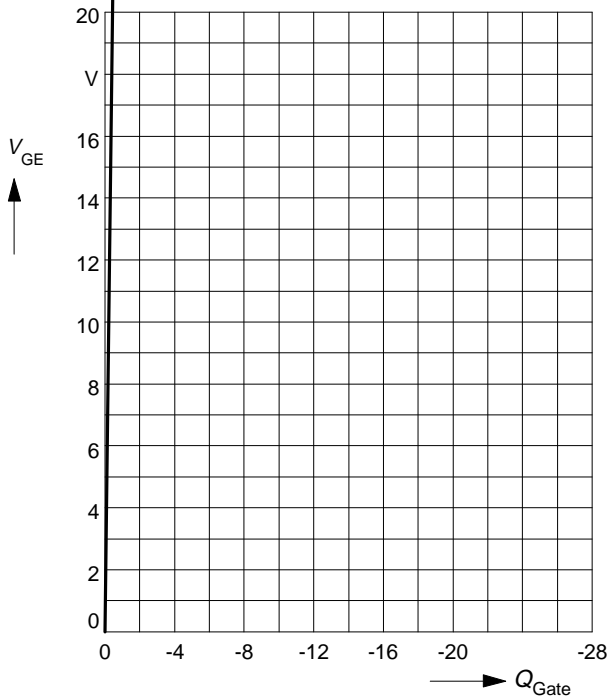
$E = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$
par.: $V_{CE}=600\text{V}$, $V_{GE} = \pm 15\text{V}$, $I_C = 8\text{ A}$



Typ. gate charge

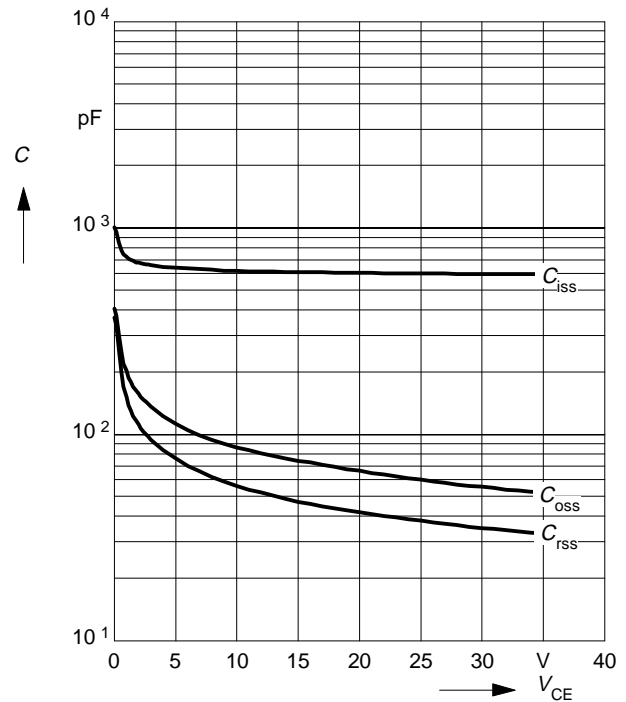
$$V_{GE} = f(Q_{Gate})$$

parameter: $I_{C\ puls} = 15\ A$



Typ. capacitances

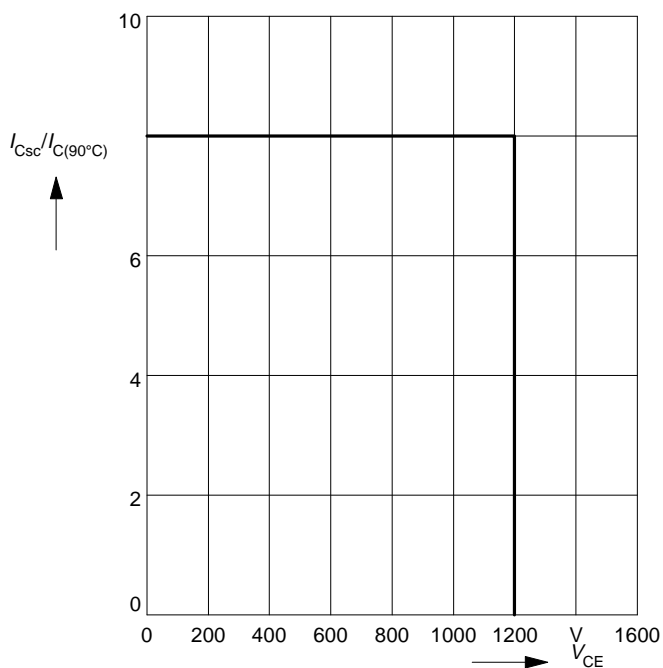
$$C = f(V_{CE})$$



Short circuit safe operating area

$$I_{Csc} = f(V_{CE}), T_j = 150^\circ C$$

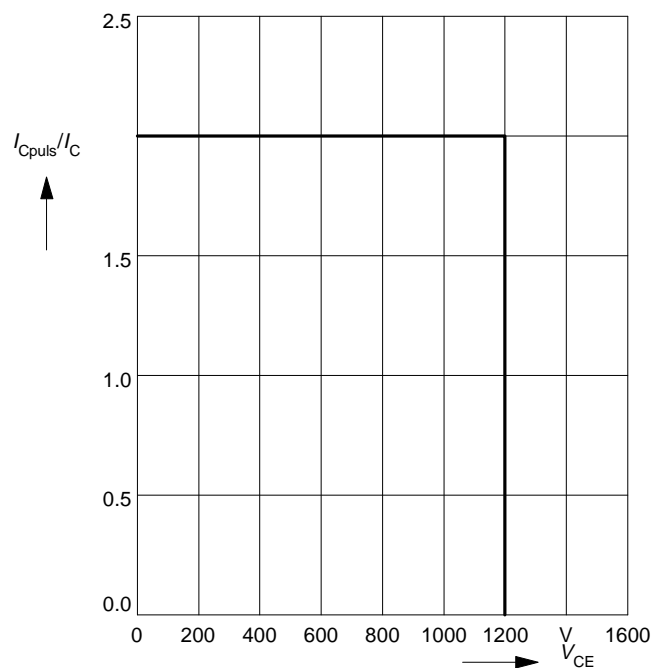
parameter: $V_{GE} = \pm 15\ V, t_{sc} \leq 10\ \mu s, L < 25\ nH$



Reverse biased safe operating area

$$I_{Cpuls} = f(V_{CE}), T_j = 150^\circ C$$

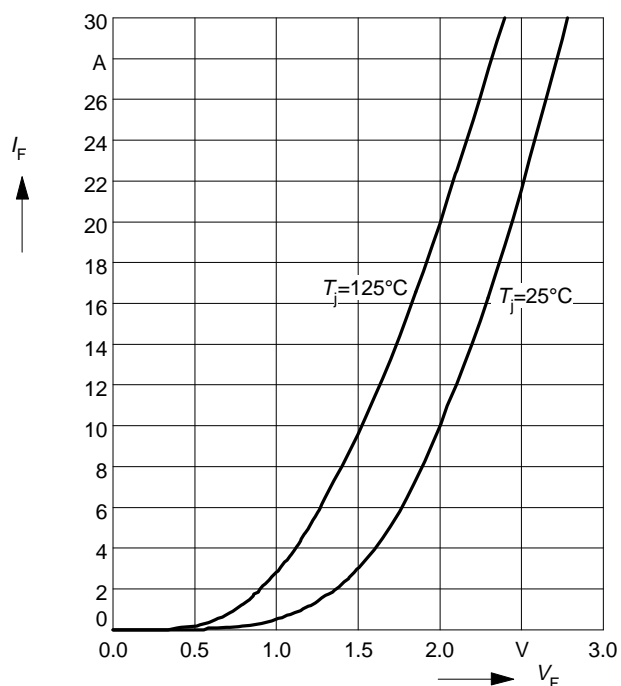
parameter: $V_{GE} = 15\ V$



Typ. forward characteristics

$$I_F = f(V_F)$$

parameter: T_j



Transient thermal impedance Diode

$$Z_{thJC} = f(t_p)$$

parameter: $D = t_p / T$

